NSN 5961-00-107-6493 Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal
Overall Length:
1.125 inches
Overall Diameter:
1.062 inches
Mounting Facility Quantity:
1
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
700.0 breakover voltage, dc
Current Rating Per Characteristic:
70.00 amperes collector current, dc
Power Rating Per Characteristic:
10.0 watts peak gate power dissipation
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 uninsulated wire lead w/terminal lug
Specification Data:
80131-release5184 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:
- -
Demilitarization:
No
Fiig:
A110a0